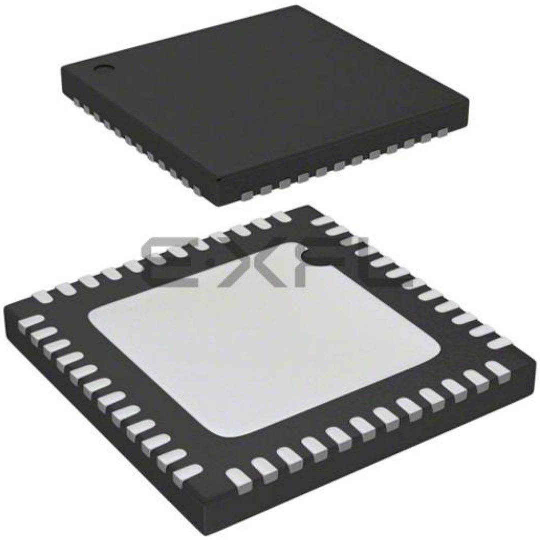


Welcome to E-XFL.COM

What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	I²C, IrDA, LINbus, SPI, UART/USART, USB
Peripherals	Brown-out Detect/Reset, Cap Sense, DMA, I²S, POR, PWM, WDT
Number of I/O	37
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 16x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	48-UFQFN Exposed Pad
Supplier Device Package	48-UFQFPN (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l151cbu6a

1 Introduction

This datasheet provides the ordering information and mechanical device characteristics of the STM32L151x6/8/B-A and STM32L152x6/8/B-A ultra-low-power ARM® Cortex®-M3 based microcontrollers product line.

The ultra-low-power STM32L151x6/8/B-A and STM32L152x6/8/B-A microcontroller family includes devices in 3 different package types: from 48 to 100 pins. Depending on the device chosen, different sets of peripherals are included, the description below gives an overview of the complete range of peripherals proposed in this family.

These features make the ultra-low-power STM32L151x6/8/B-A and STM32L152x6/8/B-A microcontroller family suitable for a wide range of applications:

- Medical and handheld equipment
- Application control and user interface
- PC peripherals, gaming, GPS and sport equipment
- Alarm systems, Wired and wireless sensors, Video intercom
- Utility metering

This STM32L151x6/8/B-A and STM32L152x6/8/B-A datasheet should be read in conjunction with the STM32L1xxxx reference manual (RM0038). The document "Getting started with STM32L1xxxx hardware development” AN3216 gives a hardware implementation overview.

Both documents are available from the STMicroelectronics website *www.st.com*.

For information on the ARM® Cortex®-M3 core please refer to the Cortex®-M3 Technical Reference Manual, available from the ARM website.

Figure 1 shows the general block diagram of the device family.

Caution: This datasheet does not apply to:
- STM32L15xx6/8/B

covered by a separate datasheet.

2.1 Device overview

Table 2. Ultra-low-power STM32L151x6/8/B-A and STM32L152x6/8/B-A device features and peripheral counts

Peripheral		STM32L15xCxxxA			STM32L15xRxxxA			STM32L15xVxxxA	
Flash (Kbytes)		32	64	128	32	64	128	64	128
Data EEPROM (Kbytes)		4							
RAM (Kbytes)		16	32	32	16	32	32	32	32
Timers	General-purpose	6							
	Basic	2							
Communication interfaces	SPI	2							
	I^2C	2							
	USART	3							
	USB	1							
GPIOs		37			51/50(1)			83	
12-bit synchronized ADC Number of channels		1 14 channels			1 20/19 channels(1)			1 24 channels	
12-bit DAC Number of channels		2 2							
LCD (STM32L152xxxxA Only) COM x SEG		4x16			4x32/4x31(1) 8x28/8x27(1)			4x44 8x40	
Comparator		2							
Capacitive sensing channels		13			20				
Max. CPU frequency		32 MHz							
Operating voltage		1.8 V to 3.6 V (down to 1.65 V at power-down) with BOR option 1.65 V to 3.6 V without BOR option							
Operating temperatures		Ambient operating temperatures: –40 to +85 °C / –40 to + 105 °C Junction temperature: -40 to +110°C							
Packages		LQFP48, UFQFPN48			LQFP64, TFBGA64			LQFP100, UFBGA100	

1. For TFBGA64 package (instead of PC3 pin there is V_{REF+} pin).

3.1 Low-power modes

The ultra-low-power STM32L151x6/8/B-A and STM32L152x6/8/B-A devices support dynamic voltage scaling to optimize its power consumption in run mode. The voltage from the internal low-drop regulator that supplies the logic can be adjusted according to the system's maximum operating frequency and the external voltage supply:

- In Range 1 (V_{DD} range limited to 1.71-3.6 V), the CPU runs at up to 32 MHz (refer to *Table 18* for consumption).
- In Range 2 (full V_{DD} range), the CPU runs at up to 16 MHz (refer to *Table 18* for consumption)
- In Range 3 (full V_{DD} range), the CPU runs at up to 4 MHz (generated only with the multispeed internal RC oscillator clock source). Refer to *Table 18* for consumption.

Seven low-power modes are provided to achieve the best compromise between low-power consumption, short startup time and available wakeup sources:

- **Sleep** mode

  In Sleep mode, only the CPU is stopped. All peripherals continue to operate and can wake up the CPU when an interrupt/event occurs.

  Sleep mode power consumption: refer to *Table 20*.
- **Low-power Run** mode

  This mode is achieved with the multispeed internal (MSI) RC oscillator set to the minimum clock (less than 131 kHz), execution from SRAM or Flash memory, and internal regulator in low-power mode to minimize the regulator's operating current. In the low-power Run mode, the clock frequency and the number of enabled peripherals are both limited.

  Low-power Run mode consumption: refer to *Table 21*.
- **Low-power Sleep** mode

  This mode is achieved by entering the Sleep mode with the internal voltage regulator in low-power mode to minimize the regulator's operating current. In the low-power Sleep mode, both the clock frequency and the number of enabled peripherals are limited; a typical example would be to have a timer running at 32 kHz.
  When wakeup is triggered by an event or an interrupt, the system reverts to the run mode with the regulator on.

  Low-power Sleep mode consumption: refer to *Table 22*.
- **Stop** mode with RTC

  Stop mode achieves the lowest power consumption while retaining the RAM and register contents and real time clock. All clocks in the V_{CORE} domain are stopped, the PLL, MSI RC, HSI RC and HSE crystal oscillators are disabled. The LSE or LSI is still running. The voltage regulator is in the low-power mode.

  The device can be woken up from Stop mode by any of the EXTI line, in 8 µs. The EXTI line source can be one of the 16 external lines. It can be the PVD output, the Comparator 1 event or Comparator 2 event (if internal reference voltage is on), it can be the RTC alarm(s), the USB wakeup, the RTC tamper events, the RTC timestamp event or the RTC wakeup.
- **Stop** mode without RTC

  Stop mode achieves the lowest power consumption while retaining the RAM and register contents. All clocks are stopped, the PLL, MSI RC, HSI and LSI RC, LSE and HSE crystal oscillators are disabled. The voltage regulator is in the low-power mode.
  The device can be woken up from Stop mode by any of the EXTI line, in 8 µs. The EXTI

Table 3. Functionalities depending on the operating power supply range (continued)

Operating power supply range	Functionalities depending on the operating power supply range			
	DAC and ADC operation	USB	Dynamic voltage scaling range	I/O operation
V_{DD} = 2.0 to 2.4 V	Conversion time up to 500 Ksps	Functional(2)	Range 1, Range 2 or Range 3	Full speed operation
V_{DD} = 2.4 to 3.6 V	Conversion time up to 1 Msps	Functional(2)	Range 1, Range 2 or Range 3	Full speed operation

1. CPU frequency changes from initial to final must respect "F_{CPU} initial < 4*F_{CPU} final" to limit V_{CORE} drop due to current consumption peak when frequency increases. It must also respect 5 µs delay between two changes. For example to switch from 4.2 MHz to 32 MHz, you can switch from 4.2 MHz to 16 MHz, wait 5 µs, then switch from 16 MHz to 32 MHz.
2. Should be USB-compliant from I/O voltage standpoint, the minimum V_{DD} is 3.0 V.

Table 4. CPU frequency range depending on dynamic voltage scaling

CPU frequency range	Dynamic voltage scaling range
16 MHz to 32 MHz (1ws) 32 kHz to 16 MHz (0ws)	Range 1
8 MHz to 16 MHz (1ws) 32 kHz to 8 MHz (0ws)	Range 2
2.1 MHz to 4.2 MHz (1ws) 32 kHz to 2.1 MHz (0ws)	Range 3

3.17 CRC (cyclic redundancy check) calculation unit

The CRC (cyclic redundancy check) calculation unit is used to get a CRC code from a 32-bit data word and a fixed generator polynomial.

Among other applications, CRC-based techniques are used to verify data transmission or storage integrity. In the scope of the EN/IEC 60335-1 standard, they offer a means of verifying the Flash memory integrity. The CRC calculation unit helps compute a signature of the software during runtime, to be compared with a reference signature generated at link-time and stored at a given memory location.

3.18 Development support

Serial wire JTAG debug port (SWJ-DP)

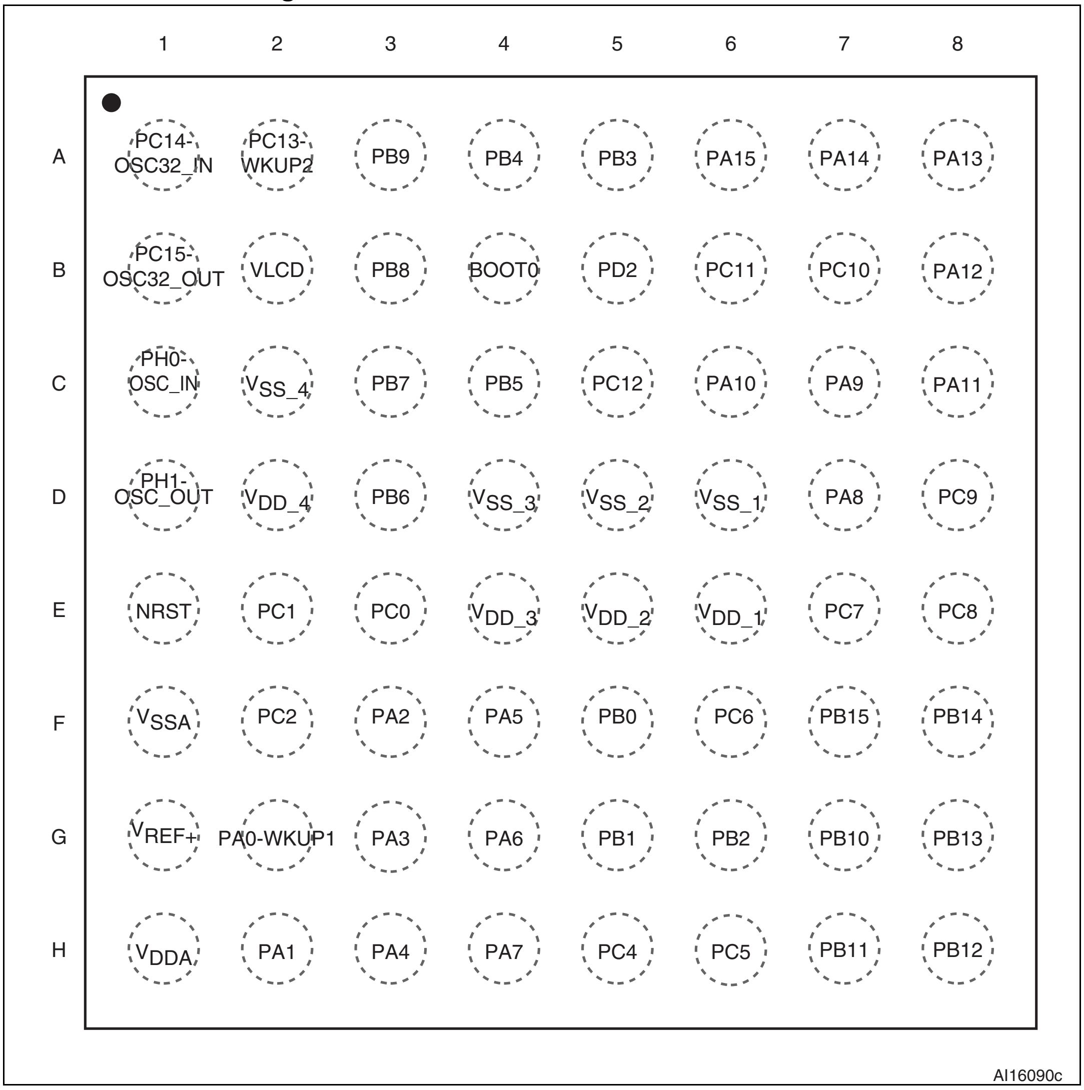
The ARM SWJ-DP interface is embedded, and is a combined JTAG and serial wire debug port that enables either a serial wire debug or a JTAG probe to be connected to the target. The JTAG JTMS and JTCK pins are shared with SWDAT and SWCLK, respectively, and a specific sequence on the JTMS pin is used to switch between JTAG-DP and SW-DP.

The JTAG port can be permanently disabled with a JTAG fuse.

Embedded Trace Macrocell™

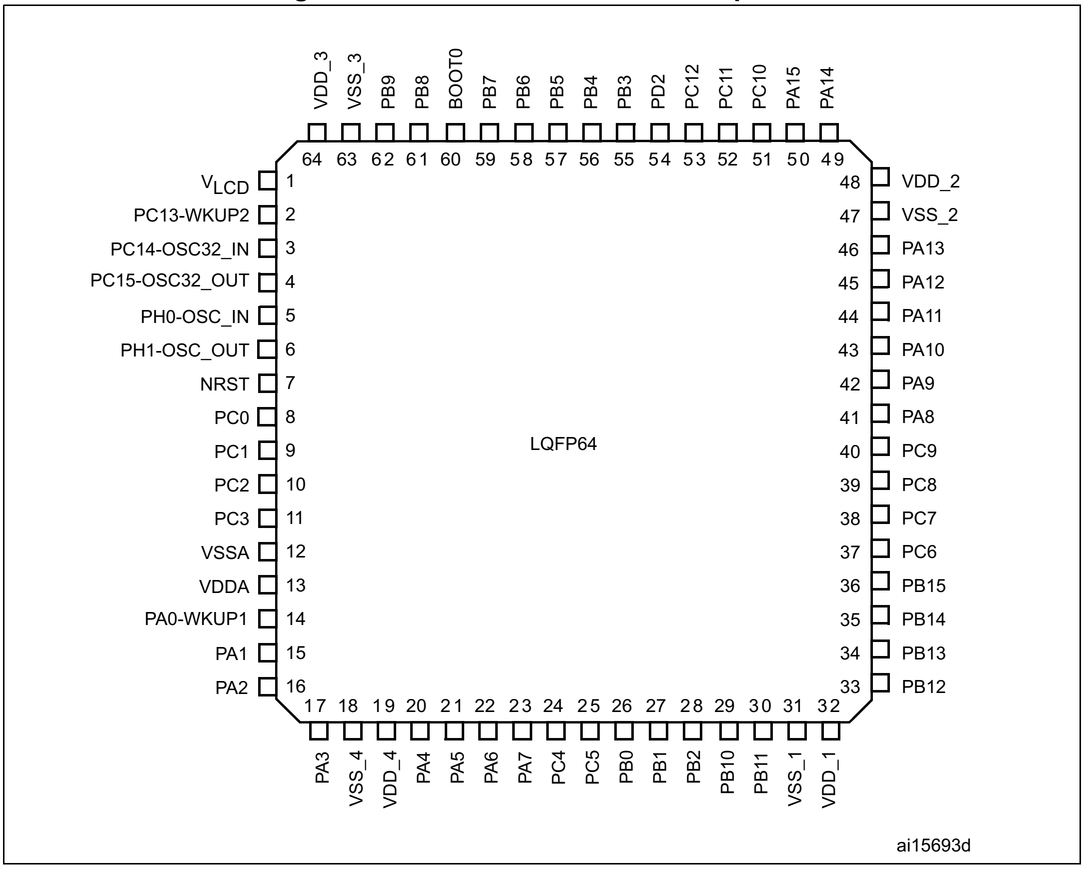
The ARM Embedded Trace Macrocell provides a greater visibility of the instruction and data flow inside the CPU core by streaming compressed data at a very high rate from the STM32L151x6/8/B-A and STM32L152x6/8/B-A device through a small number of ETM pins to an external hardware trace port analyzer (TPA) device. The TPA is connected to a host computer using USB, Ethernet, or any other high-speed channel. Real-time instruction and data flow activity can be recorded and then formatted for display on the host computer running debugger software. TPA hardware is commercially available from common development tool vendors. It operates with third party debugger software tools.

Figure 5. STM32L15xRxxxA TFBGA64 ballout



1. This figure shows the package top view.

Figure 6. STM32L15xRxxxA LQFP64 pinout



1. This figure shows the package top view.

Table 10. Alternate function input/output

Port name	Digital alternate function number														
	AFIO0	AFIO1	AFIO2	AFIO3	AFIO4	AFIO5	AFOI6	AFIO7	AFIO8	AFIO9	AFIO11	AFIO 12	AFIO 13	AFIO14	AFIO15
	Alternate function														
	SYSTEM	TIM2	TIM3/4	TIM9/10/11	I2C1/2	SPI1/2	N/A	USART 1/2/3	N/A	N/A	LCD	N/A	N/A	RI	SYSTEM
BOOT0	BOOT0	-	-	-	-	-	-	-	-	-	-	-	-	-	-
NRST	NRST	-	-	-	-	-	-	-	-	-	-	-	-	-	-
PA0-WKUP1	-	TIM2_CH1_ETR	-	-	-	-	-	USART2_CTS	-	-	-	-	-	TIMx_IC1	EVENTOUT
PA1	-	TIM2_CH2	-	-	-	-	-	USART2_RTS	-	-	[SEG0]	-	-	TIMx_IC2	EVENTOUT
PA2	-	TIM2_CH3	-	TIM9_CH1	-	-	-	USART2_TX	-	-	[SEG1]	-	-	TIMx_IC3	EVENTOUT
PA3	-	TIM2_CH4	-	TIM9_CH2	-	-	-	USART2_RX	-	-	[SEG2]	-	-	TIMx_IC4	EVENTOUT
PA4	-	-	-	-	-	SPI1_NSS	-	USART2_CK	-	-	-	-	-	TIMx_IC1	EVENTOUT
PA5	-	TIM2_CH1_ETR	-	-	-	SPI1_SCK	-	-	-	-	-	-	-	TIMx_IC2	EVENTOUT
PA6	-	-	TIM3_CH1	TIM10_CH1	-	SPI1_MISO	-	-	-	-	[SEG3]	-	-	TIMx_IC3	EVENTOUT
PA7	-	-	TIM3_CH2	TIM11_CH1	-	SPI1_MOSI	-	-	-	-	[SEG4]	-	-	TIMx_IC4	EVENTOUT
PA8	MCO	-	-	-	-	-	-	USART1_CK	-	-	[COM0]	-	-	TIMx_IC1	EVENTOUT
PA9	-	-	-	-	-	-	-	USART1_TX	-	-	[COM1]	-	-	TIMx_IC2	EVENTOUT
PA10	-	-	-	-	-	-	-	USART1_RX	-	-	[COM2]	-	-	TIMx_IC3	EVENTOUT
PA11	-	-	-	-	-	SPI1_MISO	-	USART1_CTS	-	-	-	-	-	TIMx_IC4	EVENTOUT
PA12	-	-	-	-	-	SPI1_MOSI	-	USART1_RTS	-	-	-	-	-	TIMx_IC1	EVENTOUT
PA13	JTMS-SWDIO	-	-	-	-	-	-	-	-	-	-	-	-	TIMx_IC2	EVENTOUT
PA14	JTCK-SWCLK	-	-	-	-	-	-	-	-	-	-	-	-	TIMx_IC3	EVENTOUT
PA15	JTDI	TIM2_CH1_ETR	-	-	-	SPI1_NSS	-	-	-	-	SEG17	-	-	TIMx_IC4	EVENTOUT
PB0	-	-	TIM3_CH3	-	-	-	-	-	-	-	[SEG5]	-	-	-	EVENTOUT
PB1	-	-	TIM3_CH4	-	-	-	-	-	-	-	[SEG6]	-	-	-	EVENTOUT
PB2	BOOT1	-	-	-	-	-	-	-	-	-	-	-	-	-	EVENTOUT
PB3	JTDO	TIM2_CH2	-	-	-	SPI1_SCK	-	-	-	-	[SEG7]	-	-	-	EVENTOUT

3. Negative injection disturbs the analog performance of the device. See note in *Section 6.3.17*.
4. Positive current injection is not possible on these I/Os. A negative injection is induced by V_{IN}<V_{SS}. $I_{INJ(PIN)}$ must never be exceeded. Refer to *Table 11* for maximum allowed input voltage values.
5. A positive injection is induced by V_{IN} > V_{DD} while a negative injection is induced by V_{IN} < V_{SS}. $I_{INJ(PIN)}$ must never be exceeded. Refer to *Table 11: Voltage characteristics* for the maximum allowed input voltage values.
6. When several inputs are submitted to a current injection, the maximum $\Sigma I_{INJ(PIN)}$ is the absolute sum of the positive and negative injected currents (instantaneous values).

Table 13. Thermal characteristics

Symbol	Ratings	Value	Unit
T_{STG}	Storage temperature range	–65 to +150	°C
T_J	Maximum junction temperature	150	°C
T_{LEAD}	Maximum lead temperature during soldering	see note (1)	°C

1. Compliant with JEDEC Std J-STD-020D (for small body, Sn-Pb or Pb assembly), the ST ECOPACK® 7191395 specification, and the European directive on Restrictions on Hazardous Substances (ROHS directive 2011/65/EU, July 2011).

6.3 Operating conditions

6.3.1 General operating conditions

Table 14. General operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
f_{HCLK}	Internal AHB clock frequency	-	0	32	MHz
f_{PCLK1}	Internal APB1 clock frequency	-	0	32	
f_{PCLK2}	Internal APB2 clock frequency	-	0	32	
V_{DD}	Standard operating voltage	BOR detector disabled	1.65	3.6	V
		BOR detector enabled, at power on	1.8	3.6	
		BOR detector disabled, after power on	1.65	3.6	
V_{DDA}(1)	Analog operating voltage (ADC and DAC not used)	Must be the same voltage as V_{DD}(2)	1.65	3.6	V
	Analog operating voltage (ADC or DAC used)		1.8	3.6	
V_{IN}	I/O input voltage	FT pins: 2.0 V ≤V_{DD}	–0.3	5.5(3)	V
		FT pins: V_{DD} < 2.0 V	–0.3	5.25(3)	
		BOOT0	0	5.5	
		Any other pin	–0.3	V_{DD}+0.3	

Table 20. Current consumption in Sleep mode

Symbol	Parameter	Conditions		f_{HCLK}	Typ	Max(1)	Unit
I_{DD} (Sleep)	Supply current in Sleep mode, Flash OFF	f_{HSE} = f_{HCLK} up to 16 MHz included, f_{HSE} = $f_{HCLK}/2$ above 16 MHz (PLL ON)(2)	Range 3, V_{CORE}=1.2 V VOS[1:0] = 11	1 MHz	50	155	µA
				2 MHz	78.5	235	
				4 MHz	140	370(3)	
			Range 2, V_{CORE}=1.5 V VOS[1:0] = 10	4 MHz	165	375	
				8 MHz	310	530	
				16 MHz	590	1000	
			Range 1, V_{CORE}=1.8 V VOS[1:0] = 01	8 MHz	350	615	
				16 MHz	680	1200	
				32 MHz	1600	2350	
		HSI clock source (16 MHz)	Range 2, V_{CORE}=1.5 V VOS[1:0] = 10	16 MHz	640	970	
			Range 1, V_{CORE}=1.8 V VOS[1:0] = 01	32 MHz	1600	2350	
		MSI clock, 65 kHz	Range 3, V_{CORE}=1.2 V VOS[1:0] = 11	65 kHz	19	60	
		MSI clock, 524 kHz		524 kHz	33	90	
		MSI clock, 4.2 MHz		4.2 MHz	145	210	
	Supply current in Sleep mode, Flash ON	f_{HSE} = f_{HCLK} up to 16 MHz included, f_{HSE} = $f_{HCLK}/2$ above 16 MHz (PLL ON)(2)	Range 3, V_{CORE}=1.2 V VOS[1:0] = 11	1 MHz	60.5	145	µA
				2 MHz	89.5	225	
				4 MHz	150	360	
			Range 2, V_{CORE}=1.5 V VOS[1:0] = 10	4 MHz	180	370	
				8 MHz	320	490	
				16 MHz	605	895	
			Range 1, V_{CORE}=1.8 V VOS[1:0] = 01	8 MHz	380	565	
				16 MHz	695	1070	
				32 MHz	1600	2200	
		HSI clock source (16 MHz)	Range 2, V_{CORE}=1.5 V VOS[1:0] = 10	16 MHz	650	970	
			Range 1, V_{CORE}=1.8 V VOS[1:0] = 01	32 MHz	1600	2320	
		MSI clock, 65 kHz	Range 3, V_{CORE}=1.2V VOS[1:0] = 11	65 kHz	29.5	65	
		MSI clock, 524 kHz		524 kHz	44	80	
		MSI clock, 4.2 MHz		4.2 MHz	155	220	

1. Guaranteed by characterization results, unless otherwise specified.
2. Oscillator bypassed (HSEBYP = 1 in RCC_CR register)
3. Guaranteed by test in production.

6.3.7 Internal clock source characteristics

The parameters given in the following table are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 14*.

High-speed internal (HSI) RC oscillator

Table 31. HSI oscillator characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{HSI}	Frequency	V_{DD} = 3.0 V	-	16	-	MHz
TRIM(1)(2)	HSI user-trimmed resolution	Trimming code is not a multiple of 16	-	±0.4	0.7	%
		Trimming code is a multiple of 16	-	-	±1.5	%
ACC_{HSI}(2)	Accuracy of the factory-calibrated HSI oscillator	V_{DDA} = 3.0 V, T_A = 25 °C	-1(3)	-	1(3)	%
		V_{DDA} = 3.0 V, T_A = 0 to 55 °C	-1.5	-	1.5	%
		V_{DDA} = 3.0 V, T_A = -10 to 70 °C	-2	-	2	%
		V_{DDA} = 3.0 V, T_A = -10 to 85 °C	-2.5	-	2	%
		V_{DDA} = 3.0 V, T_A = -10 to 105 °C	-4	-	2	%
		V_{DDA} = 1.65 V to 3.6 V T_A = -40 to 105 °C	-4	-	3	%
$t_{SU(HSI)}$(2)	HSI oscillator startup time	-	-	3.7	6	µs
$I_{DD(HSI)}$(2)	HSI oscillator power consumption	-	-	100	140	µA

1. The trimming step differs depending on the trimming code. It is usually negative on the codes which are multiples of 16 (0x00, 0x10, 0x20, 0x30...0xE0).
2. Guaranteed by characterization results.
3. Guaranteed by test in production.

Low-speed internal (LSI) RC oscillator

Table 32. LSI oscillator characteristics

Symbol	Parameter	Min	Typ	Max	Unit
f_{LSI}(1)	LSI frequency	26	38	56	kHz
D_{LSI}(2)	LSI oscillator frequency drift 0°C ≤ T_A ≤ 85°C	-10	-	4	%
$t_{su(LSI)}$(3)	LSI oscillator startup time	-	-	200	µs
$I_{DD(LSI)}$(3)	LSI oscillator power consumption	-	400	510	nA

1. Guaranteed by test in production.
2. This is a deviation for an individual part, once the initial frequency has been measured.
3. Guaranteed by design.

6.3.9 Memory characteristics

The characteristics are given at T_A = -40 to 105 °C unless otherwise specified.

RAM memory

Table 35. RAM and hardware registers

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
VRM	Data retention mode(1)	STOP mode (or RESET)	1.65	-	-	V

1. Minimum supply voltage without losing data stored in RAM (in Stop mode or under Reset) or in hardware registers (only in Stop mode).

Flash memory and data EEPROM

Table 36. Flash memory and data EEPROM characteristics

Symbol	Parameter	Conditions	Min	Typ	Max(1)	Unit
V_{DD}	Operating voltage Read / Write / Erase	-	1.65	-	3.6	V
t_{prog}	Programming / erasing time for byte / word / double word / half-page	Erasing	-	3.28	3.94	ms
		Programming	-	3.28	3.94	
I_{DD}	Average current during whole program/erase operation	T_A = 25 °C, V_{DD} = 3.6 V	-	300	-	µA
	Maximum current (peak) during program/erase operation		-	1.5	2.5	mA

1. Guaranteed by design.

Table 37. Flash memory, data EEPROM endurance and data retention

Symbol	Parameter	Conditions	Value			Unit
			Min(1)	Typ	Max	
NCYC(2)	Cycling (erase / write) Program memory	T_A = -40°C to 105 °C	10	-	-	kcycles
	Cycling (erase / write) EEPROM data memory		300	-	-	
t_{RET}(2)	Data retention (program memory) after 10 kcycles at T_A = 85 °C	TRET = +85 °C	30	-	-	years
	Data retention (EEPROM data memory) after 300 kcycles at T_A = 85 °C		30	-	-	
	Data retention (program memory) after 10 kcycles at T_A = 105 °C	TRET = +105 °C	10	-	-	
	Data retention (EEPROM data memory) after 300 kcycles at T_A = 105 °C		10	-	-	

1. Guaranteed by characterization results.
2. Characterization is done according to JEDEC JESD22-A117.

Input/output AC characteristics

The definition and values of input/output AC characteristics are given in *Figure 19* and *Table 45*, respectively.

Unless otherwise specified, the parameters given in *Table 45* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 14*.

Table 45. I/O AC characteristics(1)

OSPEEDRx [1:0] bit value(1)	Symbol	Parameter	Conditions	Min	Max(2)	Unit
00	$f_{max(IO)out}$	Maximum frequency(3)	C_L = 50 pF, V_{DD} = 2.7 V to 3.6 V	-	400	kHz
			C_L = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	400	
	$t_{f(IO)out}$ $t_{r(IO)out}$	Output rise and fall time	C_L = 50 pF, V_{DD} = 2.7 V to 3.6 V	-	625	ns
			C_L = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	625	
01	$f_{max(IO)out}$	Maximum frequency(3)	C_L = 50 pF, V_{DD} = 2.7 V to 3.6 V	-	2	MHz
			C_L = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	1	
	$t_{f(IO)out}$ $t_{r(IO)out}$	Output rise and fall time	C_L = 50 pF, V_{DD} = 2.7 V to 3.6 V	-	125	ns
			C_L = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	250	
10	$F_{max(IO)out}$	Maximum frequency(3)	C_L = 50 pF, V_{DD} = 2.7 V to 3.6 V	-	10	MHz
			C_L = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	2	
	$t_{f(IO)out}$ $t_{r(IO)out}$	Output rise and fall time	C_L = 50 pF, V_{DD} = 2.7 V to 3.6 V	-	25	ns
			C_L = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	125	
11	$F_{max(IO)out}$	Maximum frequency(3)	C_L = 50 pF, V_{DD} = 2.7 V to 3.6 V	-	50	MHz
			C_L = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	8	
	$t_{f(IO)out}$ $t_{r(IO)out}$	Output rise and fall time	C_L = 30 pF, V_{DD} = 2.7 V to 3.6 V	-	5	ns
			C_L = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	30	
-	t_{EXTIpw}	Pulse width of external signals detected by the EXTI controller	-	8	-	

1. The I/O speed is configured using the OSPEEDRx[1:0] bits. Refer to the reference manual for a description of GPIO Port configuration register.
2. Guaranteed by design.
3. The maximum frequency is defined in *Figure 19*.

Table 56. ADC accuracy(1)(2)

Symbol	Parameter	Test conditions	Min(3)	Typ	Max(3)	Unit
ET	Total unadjusted error	$2.4\ V \leq V_{DDA} \leq 3.6\ V$ $2.4\ V \leq V_{REF+} \leq 3.6\ V$ f_{ADC} = 8 MHz, R_{AIN} = 50 Ω T_A = -40 to 105 °C	-	2.5	4	LSB
EO	Offset error		-	1	2	
EG	Gain error		-	1.5	3.5	
ED	Differential linearity error		-	1	2	
EL	Integral linearity error		-	2	3	
ENOB	Effective number of bits	$2.4\ V \leq V_{DDA} \leq 3.6\ V$ $V_{DDA} = V_{REF+}$ f_{ADC} = 16 MHz, R_{AIN} = 50 Ω T_A = -40 to 105 °C F_{input} =10 kHz	9.5	10	-	bits
SINAD	Signal-to-noise and distortion ratio		59	62	-	dB
SNR	Signal-to-noise ratio		60	62	-	
THD	Total harmonic distortion		-	-72	-69	
ENOB	Effective number of bits	$1.8\ V \leq V_{DDA} \leq 2.4\ V$ $V_{DDA} = V_{REF+}$ f_{ADC} = 8 MHz or 4 MHz, R_{AIN} = 50 Ω T_A = -40 to 105 °C F_{input} =10 kHz	9.5	10	-	bits
SINAD	Signal-to-noise and distortion ratio		59	62	-	dB
SNR	Signal-to-noise ratio		60	62	-	
THD	Total harmonic distortion		-	-72	-69	
ET	Total unadjusted error	$2.4\ V \leq V_{DDA} \leq 3.6\ V$ $1.8\ V \leq V_{REF+} \leq 2.4\ V$ f_{ADC} = 4 MHz, R_{AIN} = 50 Ω T_A = -40 to 105 °C	-	4	6.5	LSB
EO	Offset error		-	1.5	3.5	
EG	Gain error		-	3.5	6	
ED	Differential linearity error		-	1	2	
EL	Integral linearity error		-	2.5	3.5	
ET	Total unadjusted error	$1.8\ V \leq V_{DDA} \leq 2.4\ V$ $1.8\ V \leq V_{REF+} \leq 2.4\ V$ f_{ADC} = 4 MHz, R_{AIN} = 50 Ω T_A = -40 to 105 °C	-	2	3	LSB
EO	Offset error		-	1	1.5	
EG	Gain error		-	1.5	2.5	
ED	Differential linearity error		-	1	2	
EL	Integral linearity error		-	2	3	

1. ADC DC accuracy values are measured after internal calibration.
2. ADC accuracy vs. negative injection current: Injecting a negative current on any analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative currents.
   Any positive injection current within the limits specified for $I_{INJ(PIN)}$ and $\Sigma I_{INJ(PIN)}$ in *Section 6.3.12* does not affect the ADC accuracy.
3. Guaranteed by characterization results.

Figure 26. ADC accuracy characteristics

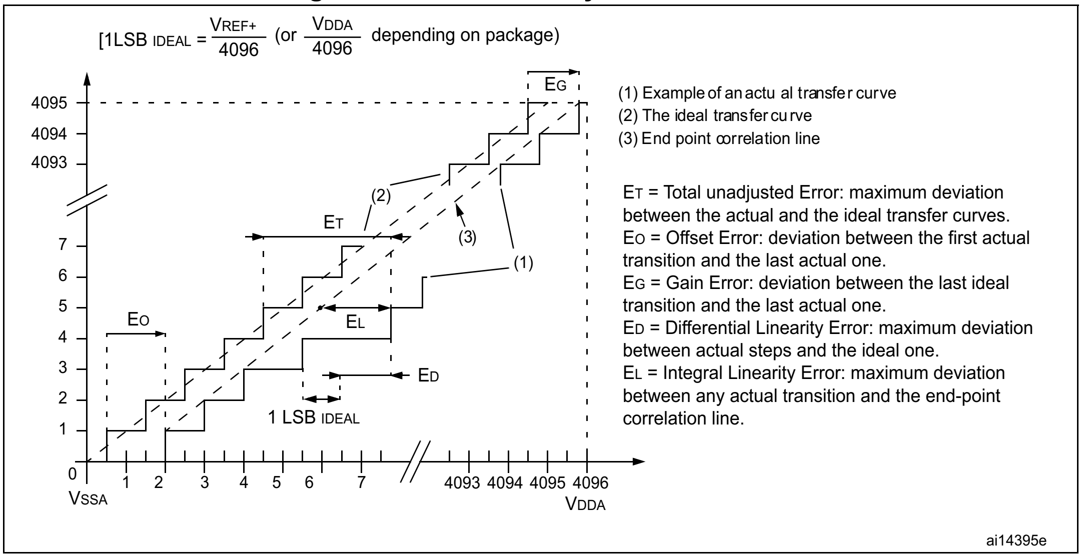
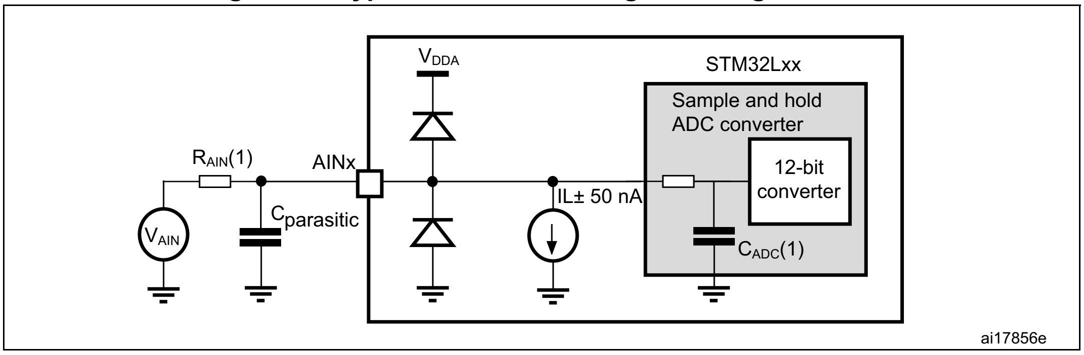


Figure 27. Typical connection diagram using the ADC

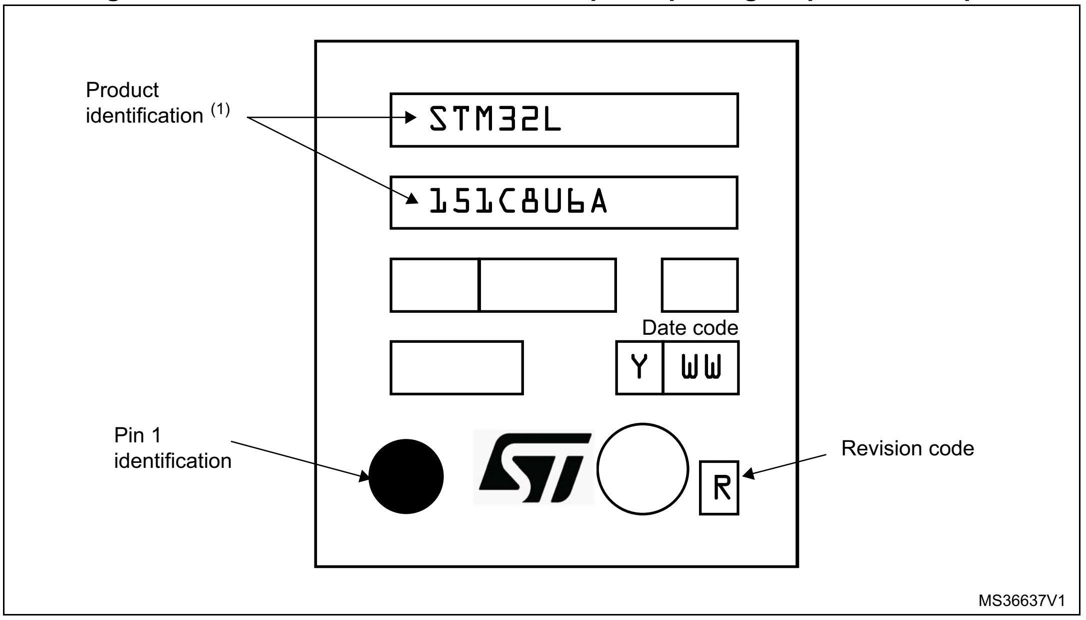


1. Refer to *Table 57: Maximum source impedance RAIN max* for the value of R_{AIN} and *Table 55: ADC characteristics* for the value of CADC
2. $C_{parasitic}$ represents the capacitance of the PCB (dependent on soldering and PCB layout quality) plus the pad capacitance (roughly 7 pF). A high $C_{parasitic}$ value will downgrade conversion accuracy. To remedy this, f_{ADC} should be reduced.

UFQFPN48 device marking

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Figure 41. UFQFPN48 7 x 7 mm, 0.5 mm pitch, package top view example



1. Parts marked as “ES”, “E” or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.

Table 68. UFBGA100 7 x 7 mm, 0.5 mm pitch, ultra thin fine-pitch ball grid array package mechanical data (continued)

Symbol	millimeters			inches(1)		
	Min	Typ	Max	Min	Typ	Max
F	0.7	0.75	0.8	0.0276	0.0295	0.0315
ddd	-	-	0.1	-	-	0.0039
eee	-	-	0.15	-	-	0.0059
fff	-	-	0.05	-	-	0.002

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 43. UFBGA100 7 x 7 mm, 0.5 mm pitch, ultra thin fine-pitch ball grid array package recommended footprint

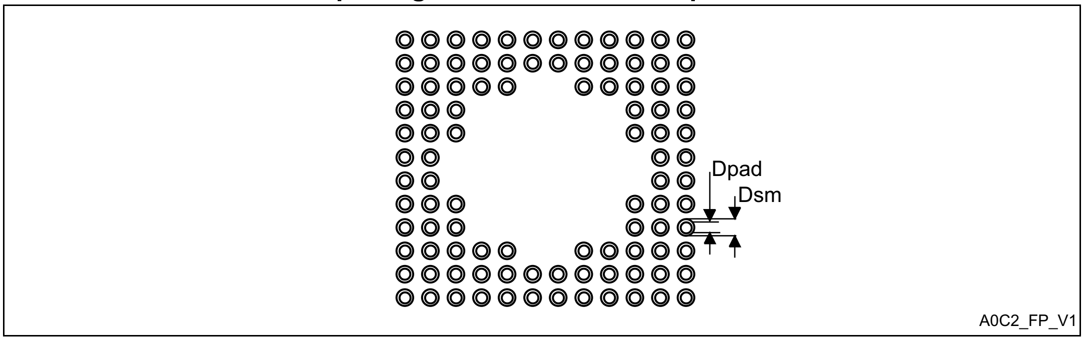
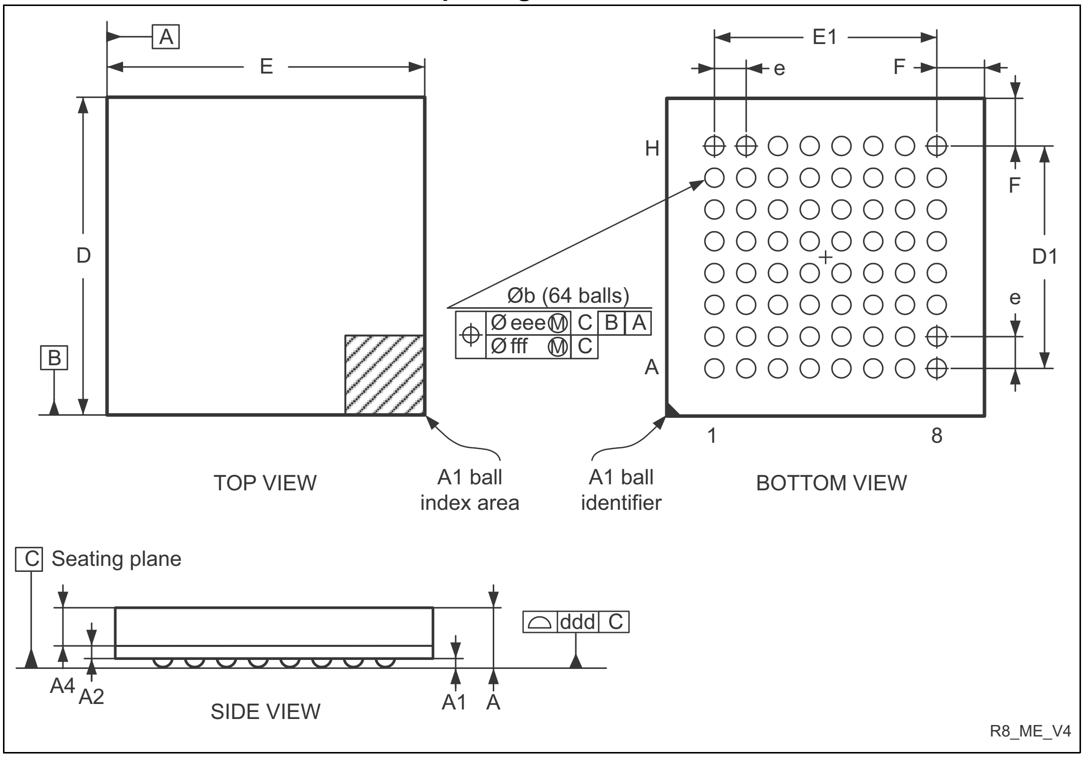


Table 69. UFBGA100 7 x 7 mm, 0.5 mm pitch, recommended PCB design rules

Dimension	Recommended values
Pitch	0.5
Dpad	0.280 mm
Dsm	0.370 mm typ. (depends on the soldermask registration tolerance)
Stencil opening	0.280 mm
Stencil thickness	Between 0.100 mm and 0.125 mm

7.6 TFBGA64 5 x 5 mm, 0.5 mm pitch, thin fine-pitch ball grid array package information

Figure 45. TFBGA64 5 x 5 mm, 0.5 mm pitch, thin fine-pitch ball grid array package outline



1. Drawing is not to scale.

Table 70. TFBGA64 5 x 5 mm, 0.5 mm pitch, thin fine-pitch ball grid array package mechanical data

Symbol	millimeters			inches(1)		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.200	-	-	0.0472
A1	0.150	-	-	0.0059	-	-
A2	-	0.200	-	-	0.0079	-
A4	-	-	0.600	-	-	0.0236
b	0.250	0.300	0.350	0.0098	0.0118	0.0138
D	4.850	5.000	5.150	0.1909	0.1969	0.2028
D1	-	3.500	-	-	0.1378	-
E	4.850	5.000	5.150	0.1909	0.1969	0.2028
E1	-	3.500	-	-	0.1378	-
e	-	0.500	-	-	0.0197	-
F	-	0.750	-	-	0.0295	-

7.7 Thermal characteristics

The maximum chip-junction temperature, T_J max, in degrees Celsius, may be calculated using the following equation:

T_J max = T_A max + (P_D max × Θ_{JA})

Where:

- T_A max is the maximum ambient temperature in °C,
- Θ_{JA} is the package junction-to-ambient thermal resistance, in °C/W,
- P_D max is the sum of P_{INT} max and $P_{I/O}$ max (P_D max = P_{INT} max + $P_{I/O}$max),
- P_{INT} max is the product of I_{DD} and V_{DD}, expressed in Watts. This is the maximum chip internal power.

$P_{I/O}$ max represents the maximum power dissipation on output pins where:

$P_{I/O}$ max = Σ (V_{OL} × I_{OL}) + Σ((V_{DD} – V_{OH}) × I_{OH}),

taking into account the actual V_{OL} / I_{OL} and V_{OH} / I_{OH} of the I/Os at low and high level in the application.

Table 72. Thermal characteristics

Symbol	Parameter	Value	Unit
Θ_{JA}	**Thermal resistance junction-ambient** UFBGA100 - 7 x 7 mm	59	°C/W
	Thermal resistance junction-ambient LQFP100 - 14 x 14 mm / 0.5 mm pitch	46	
	Thermal resistance junction-ambient TFBGA64 - 5 x 5 mm	65	
	Thermal resistance junction-ambient LQFP64 - 10 x 10 mm / 0.5 mm pitch	45	
	Thermal resistance junction-ambient LQFP48 - 7 x 7 mm / 0.5 mm pitch	55	
	Thermal resistance junction-ambient UFQFPN48 - 7 x 7 mm / 0.5 mm pitch	33	